

## DFN1006-2L ESD 静电保护二极管

### ■ Features 特点

Low Capacitance ESD Protection 低电容静电保护

- ±20kV Contact Discharge 接触放电

- ±20kV Air Discharge 空气放电

### ■ Applications 应用

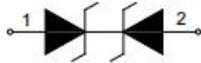
Notebooks & Handhelds 笔记本或手持机

Portable Digital Assistants 便携式数码助手

Cellular handsets and accessories 蜂窝手机及配件

Monitors and flat panel display 监视器和平板显示器

### ■ Internal Schematic Diagram 内部结构



DFN1006-2L

### ■ Absolute Maximum Ratings 最大额定值

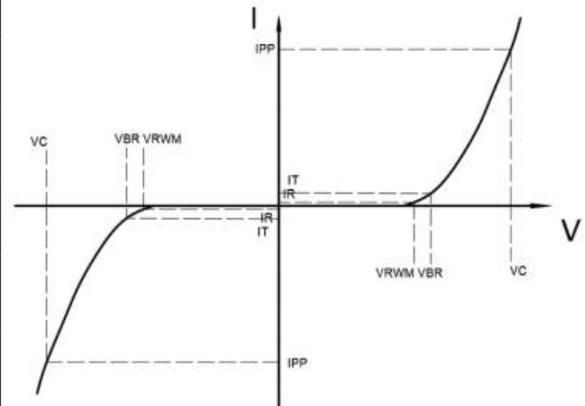
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
ESD (IEC61000-4-2 contact discharge) @25°C接触放电	$V_{ESD}$	±20	KV
ESD (IEC61000-4-2 air discharge) @25°C 空气放电	$V_{ESD}$	±20	KV
Peak Pulse Current @25°C峰值脉冲电流	$I_{PP}$	4.5	A
Peak Pulse Power @25°C峰值脉冲功率	$P_{PK}$	120	W
Lead Temperature 管脚温度	$T_L$	260	°C
Operating Temperature 工作温度	$T_{op}$	-40~125	°C
Junction Temperature 结温	$T_J$	150	°C
Storage Temperature 储存温度	$T_{stg}$	-55~150	°C

■ **Electrical Characteristics 电特性**

( $T_A=25^\circ\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ\text{C}$ )

Characteristic Parameters 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Reverse Stand-off Voltage 反向工作电压	$V_{RWM}$			5	V	
Reverse Breakdown Voltage 反向击穿电压	$V_{BR}$	6.5		9	V	$I_T=1\text{mA}$
Reverse Leakage Current 反向漏电流	$I_R$			1	$\mu\text{A}$	$V_{RWM}=5\text{V}$
Clamping Voltage 钳位电压	$V_C$		12	15	V	$I_{PP}=1\text{A}$ , $t_p=8/20\mu\text{s}$
Clamping Voltage 钳位电压	$V_C$		16	19	V	$I_{PP}=3\text{A}$ , $t_p=8/20\mu\text{s}$
Clamping Voltage 钳位电压	$V_C$		22	25	V	$I_{PP}=4.5\text{A}$ , $t_p=8/20\mu\text{s}$
Junction Capacitance 结电容	$C_J$		0.25	0.32	pF	$V_R=0\text{V}, f=1\text{MHz}$

Symbol	Parameters
$V_{RWM}$	Peak Reverse Working Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



■ Typical Characteristic Curve 典型特性曲线

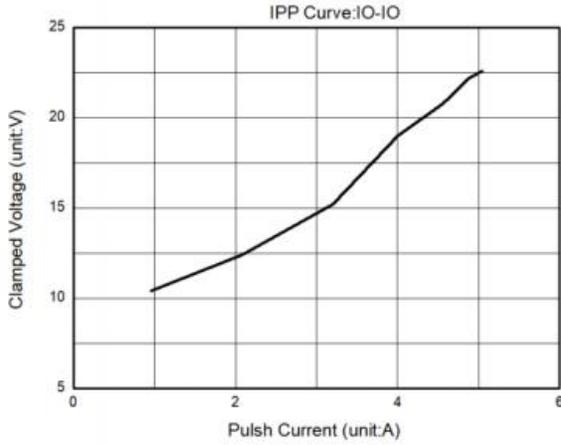


Figure 1: Clamping Voltage vs. Peak Pulse Current

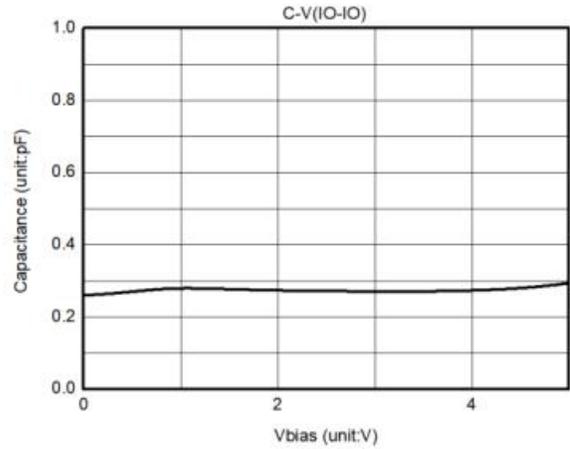


Figure 2: Junction Capacitance vs. Reverse Voltage

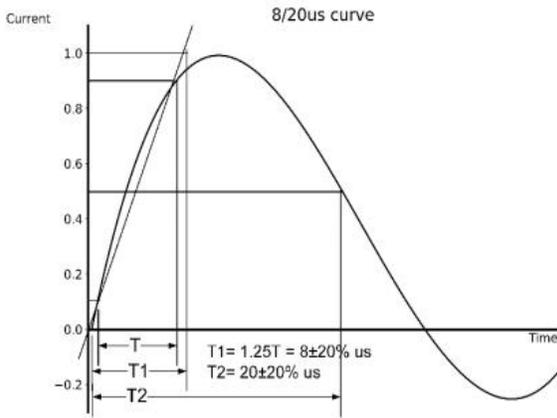


Figure 3: 8 X 20us Pulse Waveform

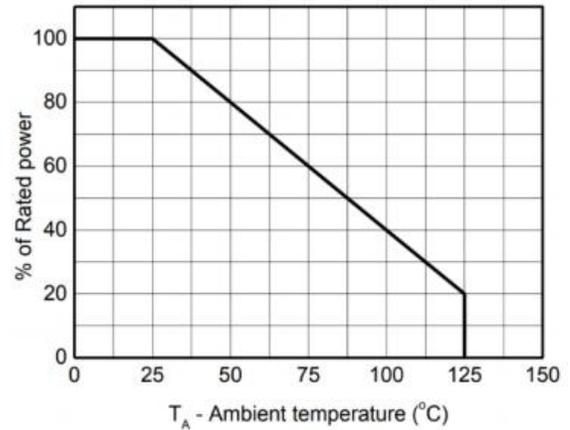


Figure 4: Power derating vs. Ambient temperature

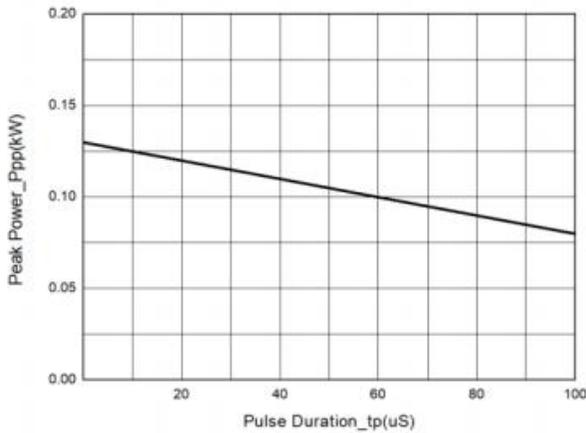


Figure 5: Peak Pulse Power vs. Pulse Time

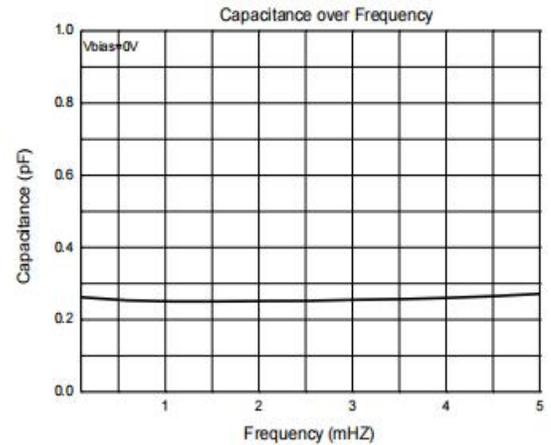
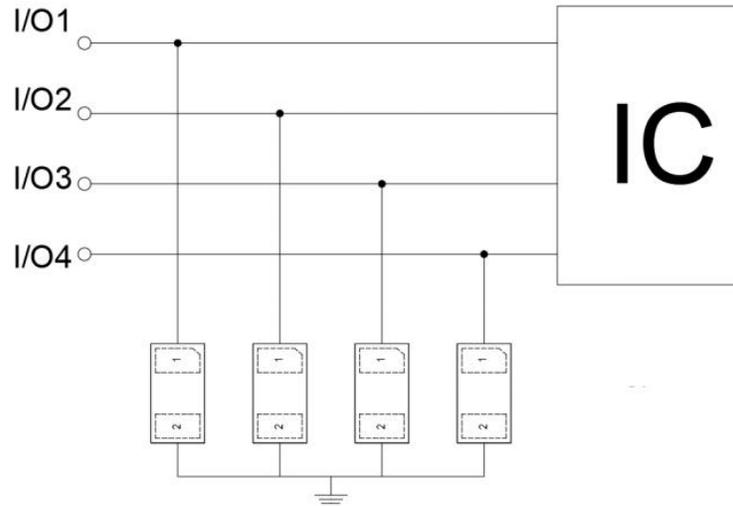
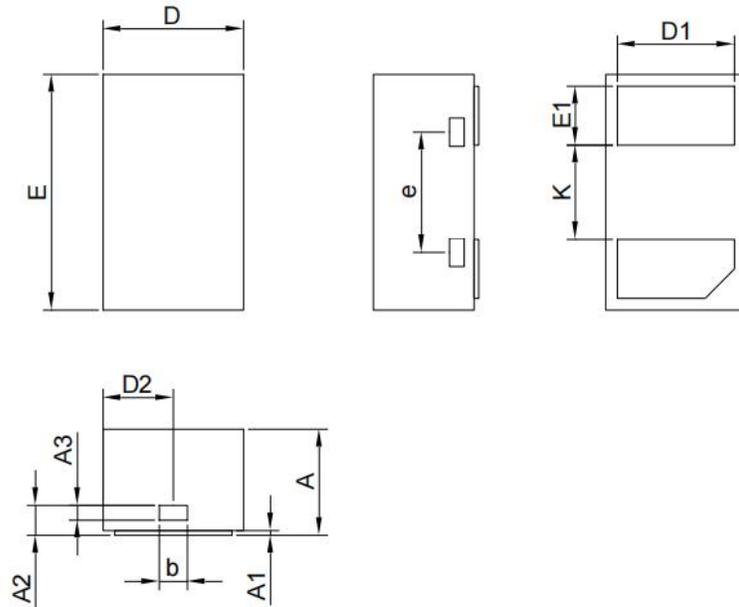


Figure 6: Capacitance over Frequency

■ Typical Applications 典型应用



■ Dimension 外形封装尺寸



Units in millimeters

Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.350	0.450	0.550	D1	0.400	0.500	0.600
A1	0.000	0.020	0.050	D2	0.200	0.300	0.400
A2	0.077	0.127	0.207	E	0.900	1.000	1.100
A3	0.013	0.063	0.113	E1	0.150	0.250	0.350
b	0.070	0.120	0.200	e	0.360	0.410	0.460
D	0.500	0.600	0.700	k	0.300	0.400	0.500